TOSHIBA Field Effect Transistor Silicon P Channel MOS Type (U-MOSVI)

TPC8120

Lithium Ion Battery Applications Power Management Switch Applications

Unit: mm

- Small footprint due to small and thin package
- Low drain-source ON-resistance: RDS (ON) = $2.6 \text{ m}\Omega$ (typ.)
- High forward transfer admittance: $|Y_{fs}| = 80 \text{ S}$ (typ.)
- Low leakage current: $IDSS = -10 \mu A (max) (VDS = -30 V)$
- Enhancement mode: $V_{th} = -0.8 \text{ to } -2.0 \text{ V (V}_{DS} = -10 \text{ V}, I_D = -1 \text{ mA)}$

Absolute Maximum Ratings (Ta = 25°C)

Characteri	stics	Symbol	Rating	Unit	
Drain-source voltage		V_{DSS}	-30	V	
Drain-gate voltage (Ro	$_{\rm SS} = 20 \; \rm k\Omega)$	V_{DGR}	-30	V	
Gate-source voltage		V_{GSS}	-25/+20	V	
Drain current	DC (Note 1)	ΙD	-18	Α	
Dialii Cuiteiii	Pulse (Note 1)	I_{DP}	-72	A	
Drain power dissipation	n (t = 10 s) (Note 2a)	P_{D}	1.9	W	
Drain power dissipation (t = 10 s) (Note 2b)		P _D	1.0	W	
Single pulse avalanche energy (Note 3)		E _{AS}	211	mJ	
Avalanche current		I _{AR}	-18	Α	
Repetitive avalanche e	energy lote 2a) (Note 4)	E _{AR}	0.03	mJ	
Channel temperature		T _{ch}	150	°C	
Storage temperature ra	ange	T _{stg}	-55 to 150	°C	

Note 1, Note 2, Note 3 and Note 4: See the next page.

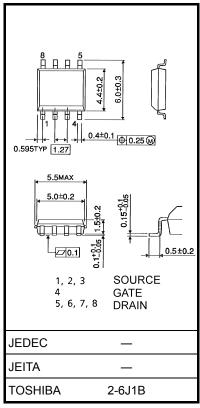
Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating

temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating

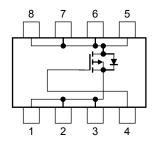
Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

This transistor is an electrostatic-sensitive device. Handle with care.



Weight: 0.080 g (typ.)

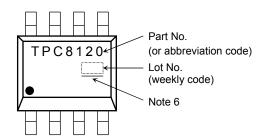
Circuit Configuration



Thermal Characteristics

Characteristics	Symbol	Max	Unit
Thermal resistance, channel to ambient (t = 10 s) (Note 2a)	R _{th (ch-a)}	65.8	°C/W
Thermal resistance, channel to ambient (t = 10 s) (Note 2b)	R _{th (ch-a)}	125	°C/W

Marking (Note 5)



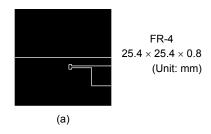
Note 6: A line under a Lot No. identifies the indication of product Labels [[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]]

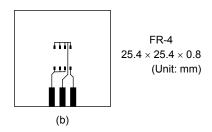
Please contact your TOSHIBA sales representative for details as to environmental matters such as the RoHS compatibility of Product. The RoHS is Directive 2002/95/EC of the European Parliament and of the Council of 27 January 2003 on the restriction of the use of certain hazardous substances in electrical and electronic equipment

Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: (a) Device mounted on a glass-epoxy board (a)

(b) Device mounted on a glass-epoxy board (b)





Note 3: $V_{DD} = -24~V$, $T_{ch} = 25^{\circ}C$ (initial), $L = 500~\mu H$, $R_G = 25~\Omega$, $I_{AR} = -18~A$

Note 4: Repetitive rating: pulse width limited by maximum channel temperature

Note 5: • on lower left of the marking indicates Pin 1.

Weekly code: (Three digits)
 Week of manufacture
 (01 for the first week of a year: sequential number up to 52 or 53)
 Year of manufacture

2

(The last digit of a year)

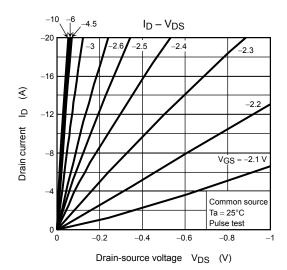
Electrical Characteristics (Ta = 25°C)

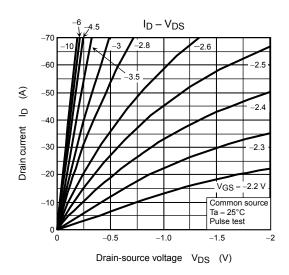
Char	Characteristics		Test Condition	Min	Тур.	Max	Unit
Gate leakage curre	ent	I _{GSS}	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$	_	_	±100	nA
Drain cut-OFF curi	rent	I _{DSS}	$V_{DS} = -30 \text{ V}, V_{GS} = 0 \text{ V}$	_	_	-10	μА
Drain-source breal	kdown woltago	V (BR) DSS	$I_D = -10 \text{ mA}, V_{GS} = 0 \text{ V}$	-30	_	_	V
Dialii-Source breat	Ruowii voitage	V _{(BR)DSX}	$I_D = -10 \text{ mA}, V_{GS} = 10V \text{ (Note 7)}$	-21	_	_	v
Gate threshold vol	tage	V _{th}	$V_{DS} = -10 \text{ V}, I_D = -1 \text{ mA}$	-0.8	_	-2.0	٧
Drain-source ON-resistance		Pro (OV)	$V_{GS} = -4.5 \text{ V}, I_D = -9 \text{ A}$	_	3.3	4.2	mΩ
Dialii-Source Oiv-i	esistance	R _{DS} (ON)	$V_{GS} = -10 \text{ V}, I_D = -9 \text{ A}$	_	2.6	3.2	1117.5
Forward transfer admittance		Y _{fs}	$V_{DS} = -10 \text{ V}, I_{D} = -9 \text{ A}$	40	80	_	S
Input capacitance		C _{iss}	V _{DS} = -10 V, V _{GS} = 0 V, f = 1 MHz	_	7420	_	pF
Reverse transfer capacitance		C _{rss}		_	1180	_	
Output capacitance		Coss		_	1440	_	
	Rise time	t _r	V _{GS}	_	10	_	
Considerable and disease	Turn-ON time	t _{on}		- ±10010 30 21 0.82.0 - 3.3 4.2 - 2.6 3.2 - 3.0 80 7420 1180 1440	_		
Switching time	Fall time	t _f	4.7 \\ \frac{4.7 \\ \trace{1.7 \\ \trinx} \\ 1.7 \\ \trace{1.7 \\ \trace{1.7 \\ \trace{1.7 \\ \trace{1.7 \\ \trace{1.7 \\	_	275	_	ns
	Turn-OFF time	t _{off}	$V_{DD} \approx -15 \text{ V}$ Duty \leq 1%, $t_W = 10 \mu\text{s}$	_	790	_	
Total gate charge (gate-source plus gate-drain)		Qg	V _{DD} ≈ -24 V, V _{GS} = -10 V,	_	180	_	nC
Gate-source charge 1		Q _{gs1}	$I_D = -18 \text{ A}$	_	20	_	
Gate-drain ("miller"	") charge	Q _{gd}		_	40	_	

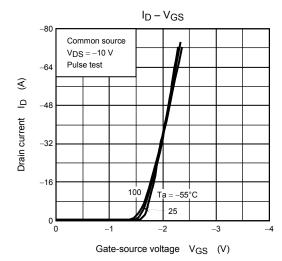
Source-Drain Ratings and Characteristics (Ta = 25°C)

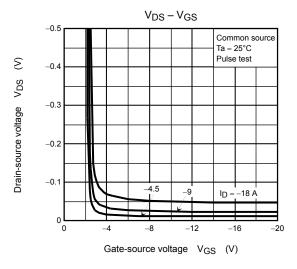
Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit	
Drain reverse current	Pulse	(Note 1)	I _{DRP}	_	_	_	-72	Α
Forward voltage (diode)		V_{DSF}	$I_{DR} = -18 \text{ A}, V_{GS} = 0 \text{ V}$	_	_	1.2	V	

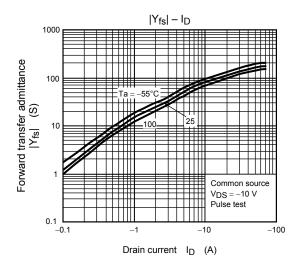
Note 7: V_{DSX} mode (the application of a plus voltage between gate and source) may cause decrease in maximum rating of drain-source voltage.

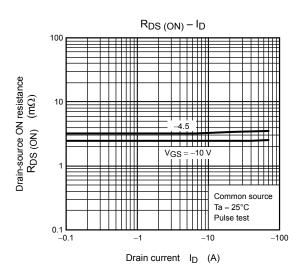


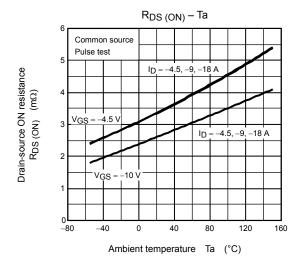


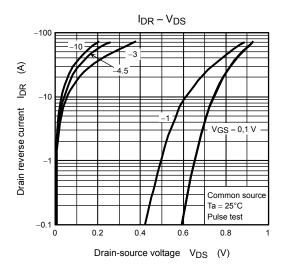


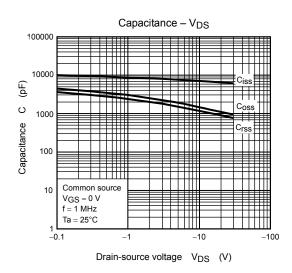


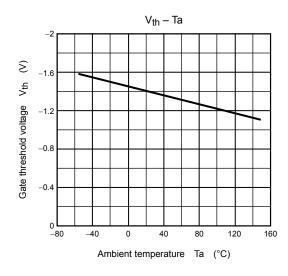


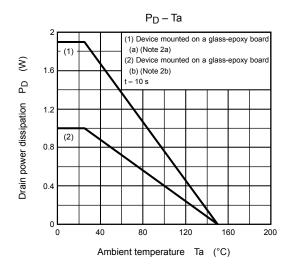


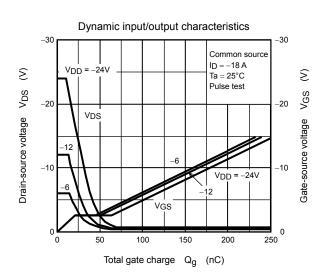


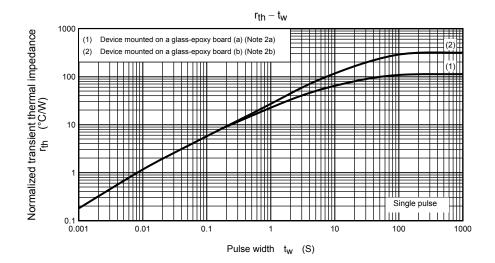


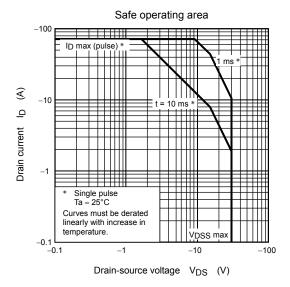












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